Agenda

#	Time	Presenter	Institute	Title of Presentation
	9:00	U. Schröder	Namlab	Welcome
		High k MIM Capacitor		
1	9:20	U. Böttger	RWTH Aachen	Electrical characterization and reliability of STO based MIM capacitors
2	9:40	B. Hudec	U. Bratislava	Low EOT TiO_2 based MIM structures for capacitor application
3	10:00	G. Ruhl	Infineon	CVD grown ternary high-k oxides for MIM capacitors
4	10:20	A. Krause	Namlab	Electrical and physical characterization of CaTiO MIM capacitors
5	10:35	A. Schmid	TU Freiberg	Dielectric relaxation behavior of high k dielectrics
	00:20	Coffee break		
		Non volatile memory		
6	11:10	J. Müller	CNT Dresden	Electrical and physical characterization of HfO based FE materials
7	11:30	K. Yurchuk	Namlab	Thickness dependence of ferroelectric HfO based materials
8	11:45	A. Kersch	H. München	Structural phases of HfO_2 and ZrO_2 from ab initio point of view
		ALD Deposition		
9	12:05	J. Niinistö	U. Helsinki	Novel ALD processes for depositing high-k Nb_2O_5 thin films
10	12:25	M. Leskala	U. Helsinki	Novel precursors for ALD of group 4 oxide thin films: TiO_2, ZrO_2, HfO_2
	01:00	Lunch at MPI - PKS		

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		RRAM		
11	13:50	M. Reiners	FZ Jülich	Atomic layer Deposition and Characterization of TiO_{2-x} Thin Films for Resistive Switches
12	14:10	C. Wenger	IHP Frankfurt/O	Resistive switching characteristics of HfO2-based 1T1R cells
13	14:30	H. Mähne	Namlab	Resistive switching of PVD TiO/NbO based cells
		Solar Applications		
14	14:50	M. Knaut/I. Dirnstorfer	IHM/Namlab	TiO_2 Electrodes for dye sensitized solar cells
15	15:10	M. Krug	IKTS/CNT	ALD deposition of passivation Layers
16	15:25	F. Benner	Namlab	Electrical characterization of Al_2O_3 based ALD passivation Layers
	00:20	Coffee break		
		ALD depostion/Characterization		
17	16:00	J. Sundqvist	CNT Dresden	ALD Lab Dresden: Hi k hardmask/High k metal gate/MIM capacitors
18	16:20	T. Henke	IHM Dresden	Flash lamp enhanced ALD
19	16:40	M. Rommel	IISB Erlangen	Electical scanning probe techniques for characterization of Hi k layers
	17:00	End		